Am93469

512 x 9 TTL Tag Buffer

ADVANCE INFORMATION

DISTINCTIVE CHARACTERISTICS

- Fast address to comparator output (MISS)
- Replaces six or more integrated circuits with a single device
- On-chip parity generator and checker
- Easy horizontal and vertical expansion
- Fully TTL compatibleIntegrated reset feature
 - 24-pin ceramic DIP (300 Mil) and Flatpak packages

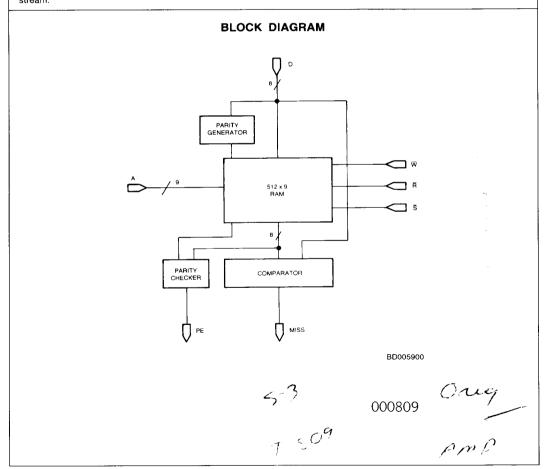
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GENERAL DESCRIPTION

The Am93469 Tag Buffer combines a 512 x 9 memory with a comparator. An internal parity generator and parity checker guarantee that no misoperation occurs.

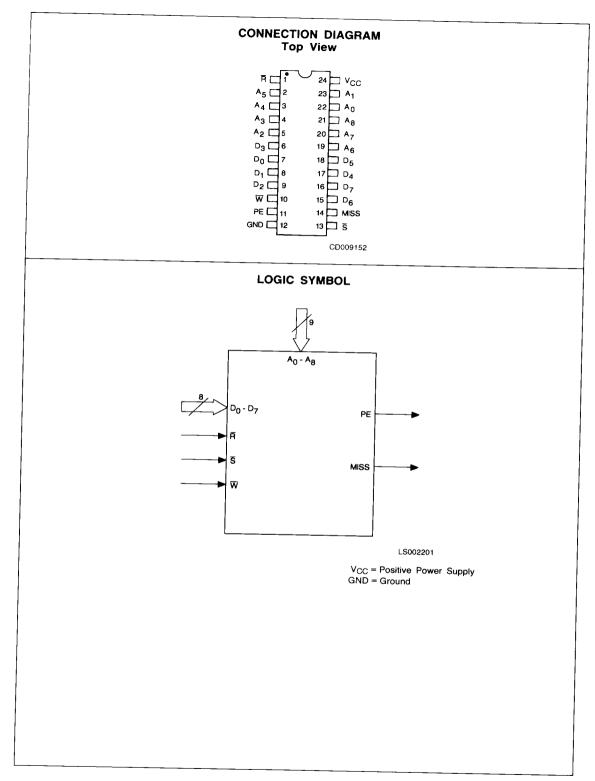
The device has three operational modes: Compare, Write, and Reset. In Compare mode, data is compared to the contents of an address location. Write mode is used to store data. Reset mode is used to clear a single 'valid bit' stream.

The Tag Buffer is designed to be used in a cache memory system for the translation of virtual addresses to physical addresses. The device can also be used in the directory and data cache. It offers state-of-the-art technology performance, while combining the functions of six or more integrated circuits into a single device.



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Order # 07562A



PIN DESCRIPTION

A₀ - A₈ Address (Inputs) Identifies memory locations.

D₀ - D₇ Data (Inputs)

During Compare cycle, eight bits of data are compared with address location given by A_0 – A_8 for equality. The result is indicated on the Comparator output pin, MISS. When \overline{W} is LOW, data is written into the address location given by A_0 – A_8 .

R Reset (Input, Active LOW)

Resets D₃ to zero.

S Chip Select (Input, Active LOW)

When S is LOW, the device is activated. A HIGH on this

input will disable the chip and force PE and MISS outputs LOW, allowing easy vertical expansion.

W Write Enable (Input, Active LOW)

Must be LOW to write Data (D_0 – D_7) into location given by A_0 – A_8 . PE output is LOW and MISS output HIGH during Write cycle.

MISS Comparator Miss (Output, Active HIGH)

LOW when Data (D_0-D_7) equals content of memory location specified by A_0-A_8 . HIGH when mismatch occurs.

PE Parity Error (Output, Active HIGH)

HIGH when the nine bits of internal data do not constitute odd parity.

FUNCTIONAL DESCRIPTION

The Am93469 Tag Buffer has three modes of operation: Compare, Write, and Reset. These modes are described as follows.

Compare Mode

The eight bits of Data inputs are compared with the content of a given memory location for equality. The nine address inputs define each memory location. In this mode, \overline{W} and \overline{R} inputs are HIGH, and \overline{S} is LOW. If the eight bits of Data inputs are exactly the same as the eight bits of data in the given memory location, the MISS output will be LOW. If not, the MISS output will be HIGH. The parity bit is not compared.

Write Mode

The eight bits of data inputs and the one bit of parity are written into the RAM array when both \overline{S} and \overline{W} are LOW, and \overline{R} is HIGH. The MISS output is forced HIGH (the MISS output is associated with the output enable of the data cache). The Parity Error (PE) output is forced LOW.

Reset Mode

When \overline{R} = LOW, \overline{S} = LOW, and \overline{W} = HIGH, a dedicated section of the entire array, D₃, is reset to LOW. The PE output is forced LOW during reset. The MISS output is forced HIGH. All 512 D₃ data bits are reset to a low state. The other seven bits in each address location may change to an undetermined state (HIGH or LOW).

TABLE 1. FUNCTION TABLE

	INPUTS OUTPUTS			
	<u>s</u> =	Diameter of	IISS	DESCRIPTION
- Me	market or	(rum o sign	,	Disabled
		nemory ?	SS ATCH	Compare
	. walk			Reset
, ,	(3 3/C P)* 32	E	1CL	Write
m 116	. 16 M. J. James	*** 1		Illegal
3) " 460	nu-, (=12×9)	Type!		
		m fell	$f_I \in \mathcal{I}$	
51	2×1 6	grades of the state of the stat		

ABSOLUTE MAXIMUM RATINGS

Storage Temperature65 to +150°C
Ambient Temperature with
Power Applied – 55 to + 125°C
Suply Voltage0.5 to +7.0 V
DC Voltage Applied to Outputs0.5 to VCC Max
DC Input Voltage0.5 to +5.5 V
DC Input Current

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Device	es
Temperature (T _A)	0 to +75°C
Supply Voltage (VC	c)+4.75 to +5.25 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified

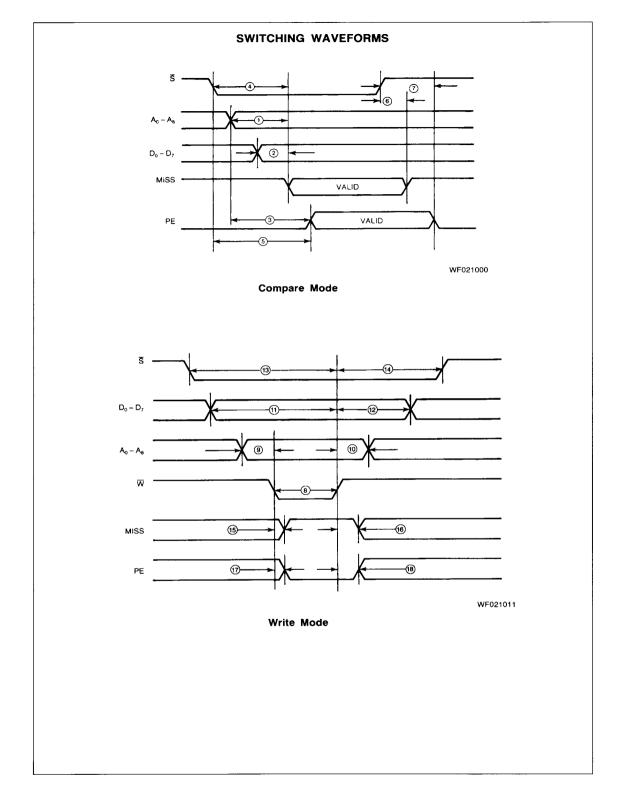
Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Units
V _{OH}	Output HIGH Voltage	I _{OH} = -5.2 mA	2.4		V
V _{OL}	Output LOW Voltage	OL = 16 mA		0.45	V
V _{IH}	Input HIGH Voltage		2.0		V
V _{IL}	Input LOW Voltage			0.8	V
V _{CL}	Input Clamp Voltage	i _{IN} = -10 mA		→ 1.5	V
l _{IL}	Input LOW Current	V _{IN} = 0.4 V		-400	μΑ
Iн	Input HIGH Current	V _{IN} = 4.5 V		40	μΑ
I _{SC} (Note 1)	Output Short-Circuit Current	V _{OUT} = 0.0 V		- 100	mA
Icc	Supply Current			185	mA

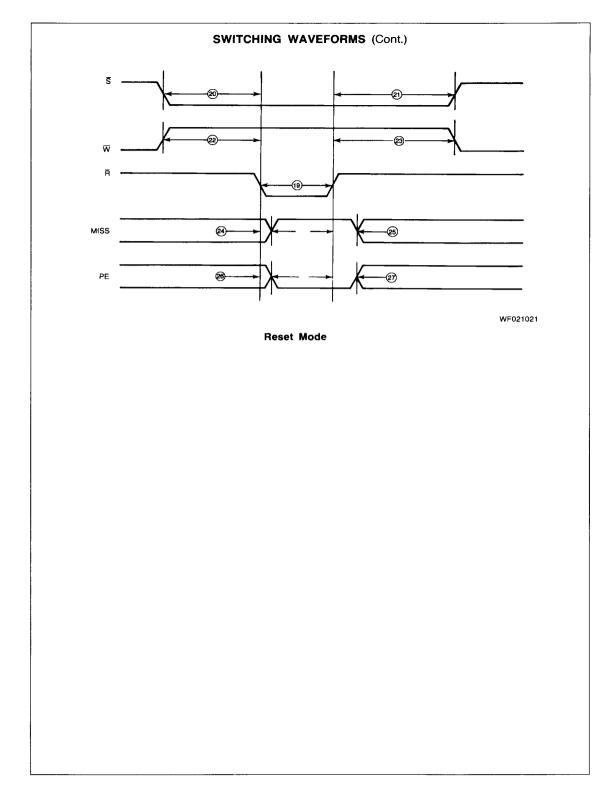
Notes: 1. No more than one output should be short circuited at a time. The duration of the short circuit should not be more than one second.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified (Note 1)

No.	Parameter Symbol	Parameter Description	Min.	Max.	Units
Compare	Mode				
1	†AVMV	Address to MISS		20.0	ns
2	†DVMV	Data to MISS		7.0	ns
3	tavpv	Address to PE		20.0	ns_
4	tslmv	S to MISS		7.0	ns
5	tSLPV	S to PE		7.0	ns
6	t _{SHML}	S to MISS Recovery		7.0	ns
7	tshpl	S to PE Recovery		7.0	ns
Write Mo	de				
8	twLwH	Write Pulse Width	15.0		ns
9	tavwl	Address Setup	3.0		ns
10	twhax	Address to W Hold	2.0		ns
11	tDVWH	Data to W Setup	18.0		ns
12	twhpx	Data to W Hold	2.0		ns
13	tslwh	S to Setup	18.0		ns
14	twhsh	S to Select Hold	2.0		ns
15	twlmh	W to MISS		7.0	ns
16	twhmx	Write Recovery (MISS)		22.0	ns
17	twlpl	W to PE		7.0	ns
18	twhex	Write Recovery (PE)		22.0	ns
Reset Mo	ode				
19	t _{RLRH}	R Pulse Width	50.0		ns
20	tSLRL	S to R Setup	5.0		ns
21	tRHSH	S to R Hold	10.0		ns
22	twhrl	W to R Setup	5.0		ns
23	t _{RHWL}	W to R Hold	10.0		ns
24	^t RLMH	R to MISS HIGH		7.0	ns
25	tahmx	R to MISS Recovery		22.0	ns
26	t _{RLPL}	R to PE LOW		7.0	ns
27	tehex	R to PE Recovery		22.0	ns

Notes: 1. All Switching Characteristics are measured at 50% of input to valid output. Both input and output timings are referenced to 1.5 V.

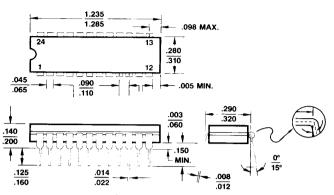




PHYSICAL DIMENSIONS

CD3024





PID # 06850A

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